SEMI® International Standards Program

Compound Semiconductor Technical Committee Meeting

Room: Office “Staffelsee”
Internationales Congress Center München, Germany

Thursday 20th Nov 2025,
09:00-10:30 CET

V3 03.11.2025
Co-chairs:

- Dr. Arnd-Dietrich Weber, SiCrystal
- Dr. Christian Kranert, IISB Fraunhofer

European Compound Semiconductor Committee Meeting ***(Hybrid Meeting)***

09:00	**Welcome and Self-Introductions**	**all**
09:05	SEMI Standards Overview and Legal Reminders	SEMI Staff
09:10	Review of the minutes and action items from the previous meeting	SEMI Staff
09:15	Task Force Reports (~5 minutes each) • SiC-Task Force (M81 Review) • 5-year Review Task Force (inactive) • Test Method for SiC -Task Force • SiC Epi Defects Task Force • Silicon Carbide Engineered Substrate Task Force	 A. Weber H.C. Alt C. Kranert C. Kranert E. Cela
09:40	Ballot Authorization • Doc. 7111 Revision of M81: Guide to Defects found on monocrystalline Silicon Carbide substrates	 A. Weber
09:55	5y Review: Identify published documents due to 5y Review M82-0820: Test Method for the Carbon Acceptor Concentration in Semi-Insulating Gallium Arsenide Single Crystals by Infrared Absorption Spectroscopy M55-0921: Specification for Polished Monocrystalline Silicon Carbide Wafers	A. Weber
10:05	Compound Materials Liaison Reports • North America • Japan • China	 SEMI Staff
10:15	New Business: • Open Discussion	 N.N.
10:20	Any Other Business / Questions	A. Weber
10:25	Next Meeting	
10:30	End	